

NSA5.0AFT3G

400 Watt Peak Power Zener Transient Voltage Suppressor

Unidirectional

The NSA5.0AFT3G is designed to protect voltage sensitive components from high voltage, high energy transients. It has excellent clamping capability, high surge capability, low zener impedance and a fast response time. The NSA5.0AFT3G is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Features

- Peak Power – 400 W @ 1 ms
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- ESD Rating IEC 61000-4-2 (> 30 kV)
- Response Time is Typically < 1 ns
- Flat Handling Surface for Accurate Placement
- Package Design for Top Slide or Bottom Circuit Board Mounting
- Low Profile Package
- This is a Pb-Free Device

Mechanical Characteristics:

CASE: Void-free, transfer-molded plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260°C for 10 Seconds

POLARITY: Cathode indicated by molded polarity notch or polarity band

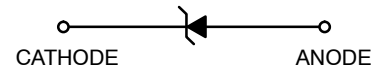
MOUNTING POSITION: Any



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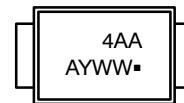
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PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSOR 400 W PEAK POWER



**SMA-FL
CASE 403AA**

MARKING DIAGRAM



- 4AA = Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NSA5.0AFT3G	SMA-FL (Pb-Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 2 of this data sheet.

NSA5.0AFT3G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L = 25^\circ\text{C}$, Pulse Width = 1 ms	P_{PK}	400	W
DC Power Dissipation @ $T_L = 75^\circ\text{C}$ Measured Zero Lead Length (Note 2) Derate Above 75°C	P_D	1.5	W
Thermal Resistance from Junction to Lead	$R_{\theta JL}$	20	$\text{mW}/^\circ\text{C}$
		50	$^\circ\text{C}/\text{W}$
DC Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	0.5	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	4.0	$\text{mW}/^\circ\text{C}$
		250	$^\circ\text{C}/\text{W}$
Forward Surge Current (Note 4) @ $T_A = 25^\circ\text{C}$	I_{FSM}	40	A
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

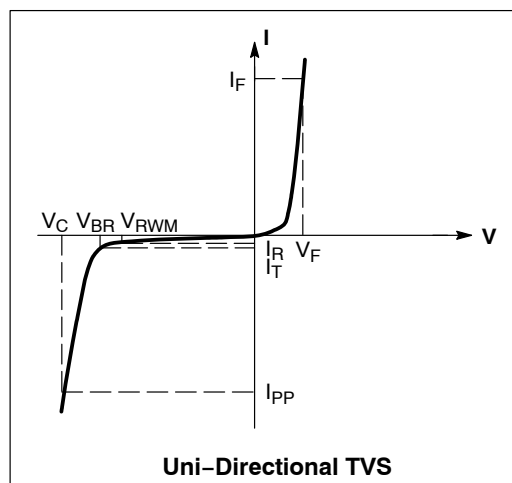
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 10 X 1000 μs , non-repetitive.
- 1" square copper pad, FR-4 board.
- FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403AA case outline dimensions spec.
- 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F



ELECTRICAL CHARACTERISTICS

Device	Device Marking	V_{RWM} (Note 5) Volts	I_R @ V_{RWM} μA	Breakdown Voltage			V_C @ I_{PP} (Note 7)		C Typ. (Note 8) pF	V_F @ I_F (Note 9)	
				V_{BR} (Volts) (Note 6)			V_C	I_{PP}		Max	
				Min	Nom	Max	mA	Volts	Amps	V	
NSA5.0AFT3G	QA	5.0	400	6.4	6.7	7.0	10	9.2	43.5	2450	3.5

- A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
- V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C .
- Surge current waveform per Figure 2 and derate per Figure 3.
- Bias voltage = 0 V, F = 1.0 MHz, $T_J = 25^\circ\text{C}$.
- 1/2 sine wave or equivalent, PW = 8.3 ms, non-repetitive, $I_F = 30$ A.

RATING AND TYPICAL CHARACTERISTIC CURVES

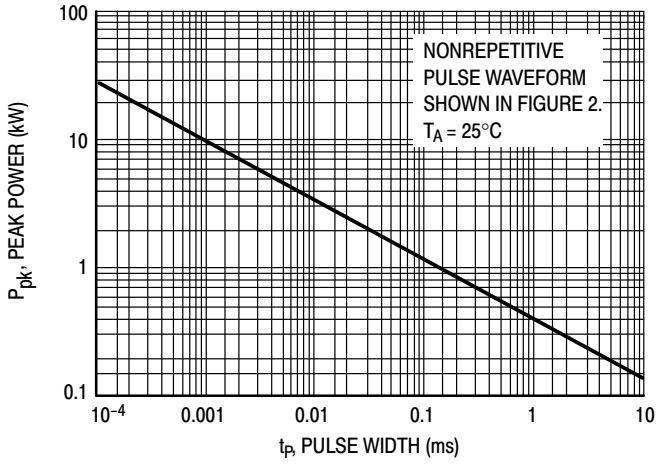


Figure 1. Pulse Rating Curve

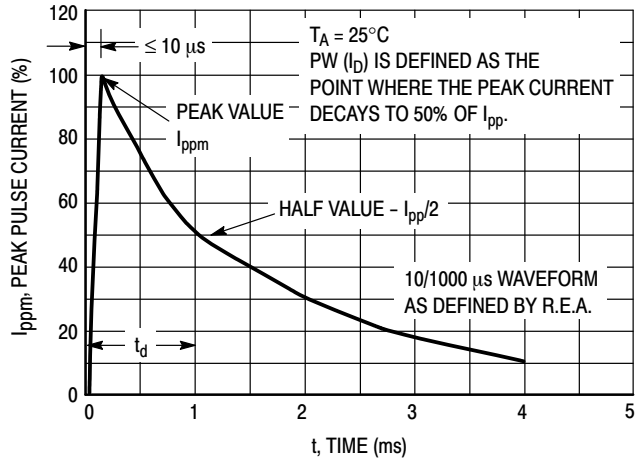


Figure 2. Pulse Waveform

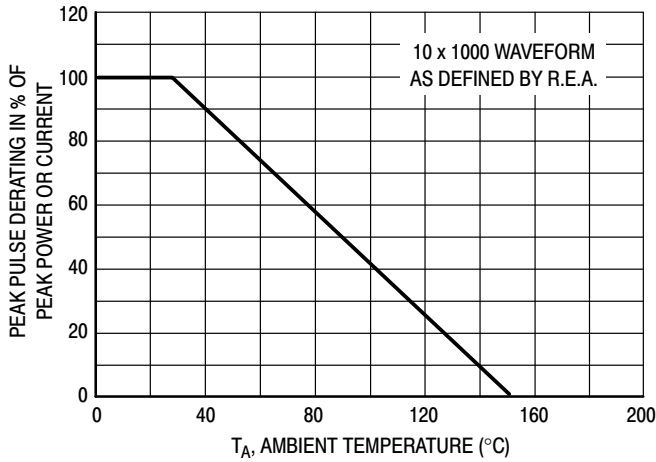


Figure 3. Pulse Derating Curve

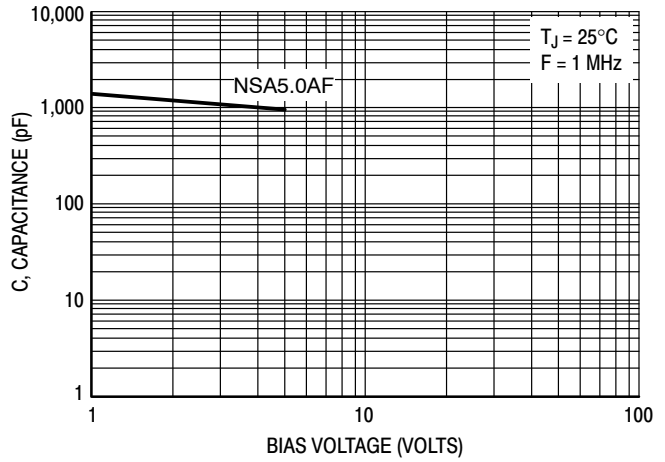


Figure 4. Typical Junction Capacitance vs. Bias Voltage

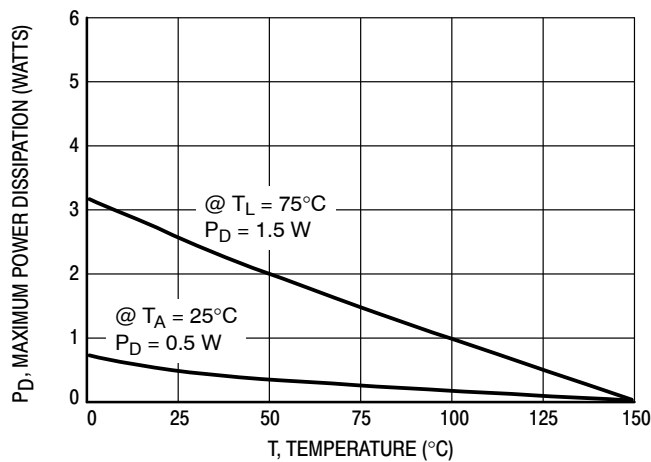
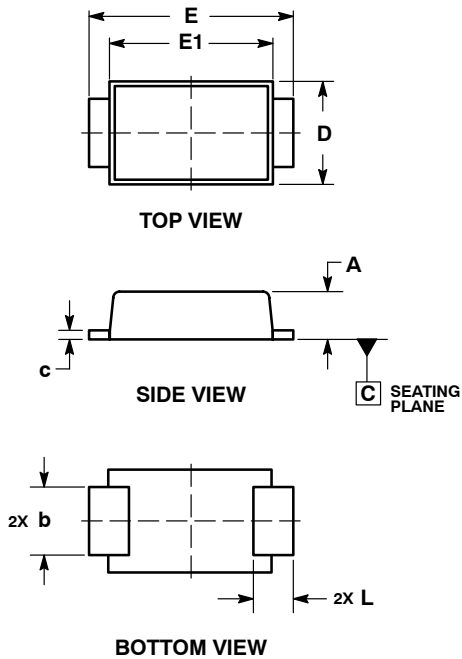


Figure 5. Steady State Power Derating

NSA5.0AFT3G

PACKAGE DIMENSIONS

SMA-FL
CASE 403AA-01
ISSUE O

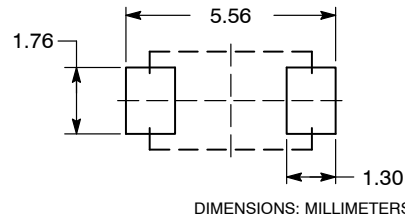


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	1.25	1.65
c	0.15	0.30
D	2.40	2.80
E	4.80	5.40
E1	4.00	4.60
L	0.70	1.10

RECOMMENDED SOLDER FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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